

BD244/A/B/C

Medium Power Linear and Switching Applications

• Complement to BD243, BD243A, BD243B and BD243C respectively



1.Base 2.Collector 3.Emitter

Rev. A, February 2000

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: BD244	- 45	V
	: BD244A	- 60	V
	: BD244B	- 80	V
	: BD244C	- 100	V
V _{CEO}	Collector-Emitter Voltage		
	: BD244	- 45	V
	: BD244A	- 60	V
	: BD244B	- 80	V
	: BD244C	- 100	V
V _{EBO}	Emitter-Base Voltage	- 5	V
I _C	Collector Current (DC)	- 6	А
I _{CP}	*Collector Current (Pulse)	- 10	А
I _B	Base Current	- 2	А
P _C	Collector Dissipation (T _C =25°C)	65	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaining Voltage					_
	: BD244	$I_C = -30 \text{mA}, I_B = 0$	- 45			V
	: BD244A		- 60			V
	: BD244B		- 80			V
	: BD244C		- 100			V
I _{CEO}	Collector Cut-off Current : BD244/244A	$V_{CE} = -30V, I_{B} = 0$			- 0.7	mA
	: BD244B/244C	$V_{CE} = -60V, I_{B} = 0$			- 0.7	mA
I _{CES}	Collector Cut-off Current : BD244	$V_{CE} = -45V, V_{BE} = 0$			- 0.4	mA
	: BD244A	$V_{CE} = -60V, V_{BE} = 0$			- 0.4	mA
	: BD244B	$V_{CE} = -80V, V_{BE} = 0$			- 0.4	mA
	: BD244C	$V_{CE} = -100V, V_{BE} = 0$			- 0.4	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 1	mA
h _{FE}	* DC Current Gain	$V_{CE} = -4V, I_{C} = -0.3A$	30			
		$V_{CE} = -4V, I_{C} = -3A$	15			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = -6A, I_B = -1A$			- 1.5	V
V _{BE} (on)	* Base-Emitter ON Voltage	$V_{CE} = -4V, I_{C} = -6A$			- 2	V
* Pulse Test: PW =300µs, duty Cycle =2% Pulsed						

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Typical Characteristics

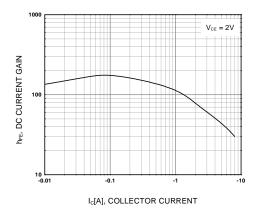


Figure 1. DC current Gain

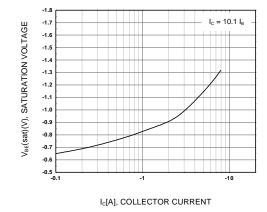


Figure 2. Base-Emitter Saturation Voltage

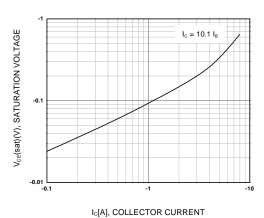


Figure 3. Collector-Emitter Saturation Voltage

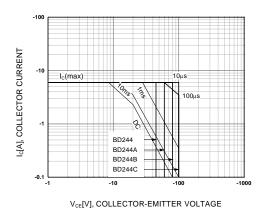


Figure 4. Safe Operating Area

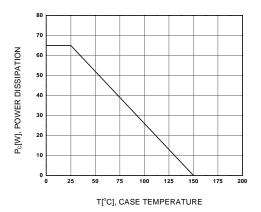
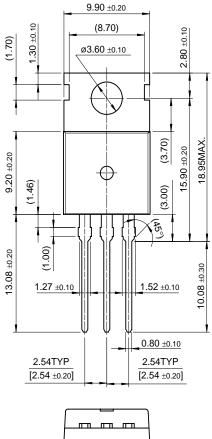


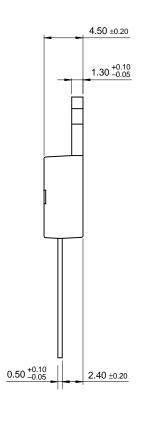
Figure 5. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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